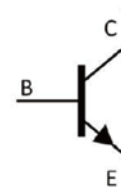


Features

- Low frequency, low noise pre-amplifier.
- High PC and hFE, excellent hFE linearity.



SOT23



Equivalent Circuit

Absolute Maximum Ratings(T_A=25℃)

Symbol	Parameter	Value	Uniat
V _{CBO}	Collector-Base Voltage	50	V
V _{CEO}	Collector-Emitter Voltage	45	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	0.1	A
P _C	Collector Power Dissipation	200	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	625	°C/W
T _J , T _{stg}	Operation Junction And Storage Temperature Range	-55 ~ +150	°C/W

Electrical Characteristics (T_A=25℃ unless otherwise specified)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =100μA, I _E =0	50			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =100mA, I _B =0	45			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =100μA, I _C =0	5			V
I _{CEO}	Collector cut-off current	V _{CE} =35V, I _E =0			1	nA
I _{CBO}	Collector cut-off current	V _{CB} =50V, I _E =0			100	nA
I _{EBO}	Emitter cut-off current	V _{EB} =3V, I _C =0			100	nA
h _{FE(1)}	DC current gain(1)	V _{CE} =5V, I _C =1mA	200		450	
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =100mA, I _B =5mA			0.3	V
V _{BE(sat)}	Base-emitter saturation voltage				1.0	V
f _T	Transition frequency	V _{CE} =5V, I _C =10mA, f=30MHz	150			MHz

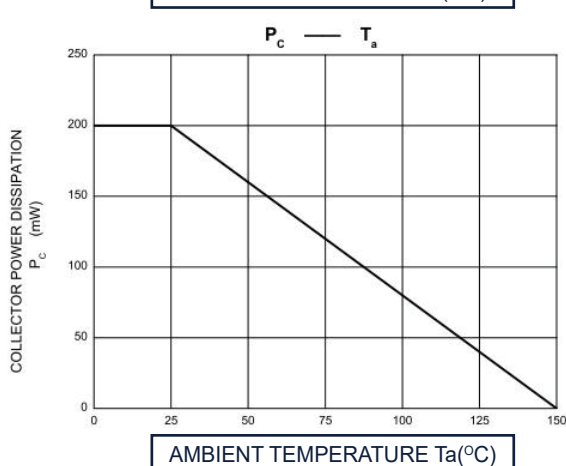
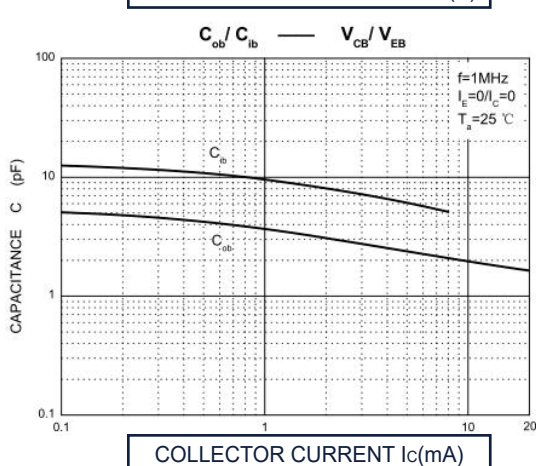
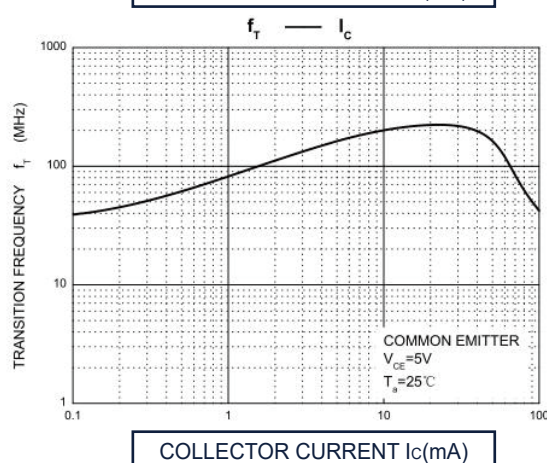
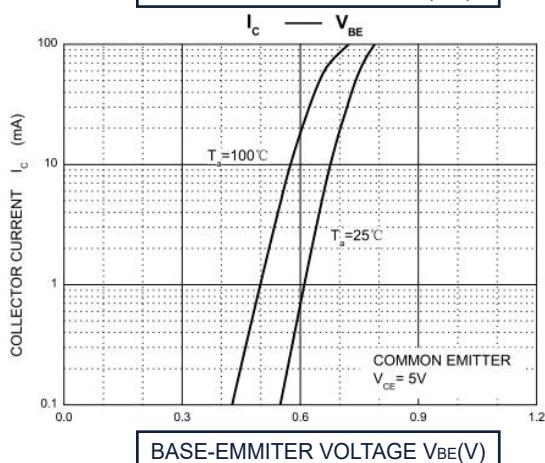
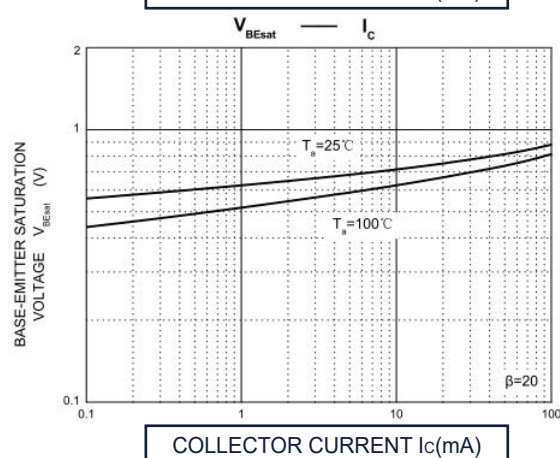
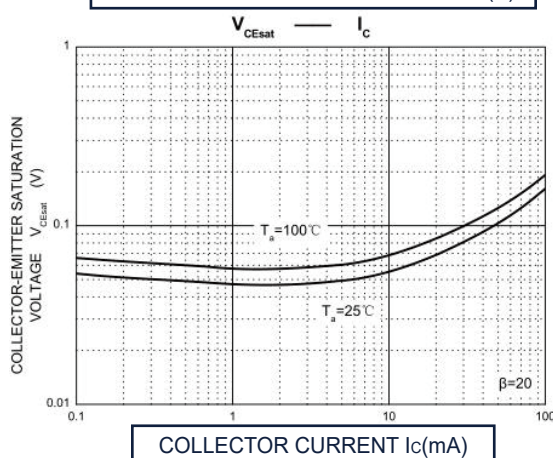
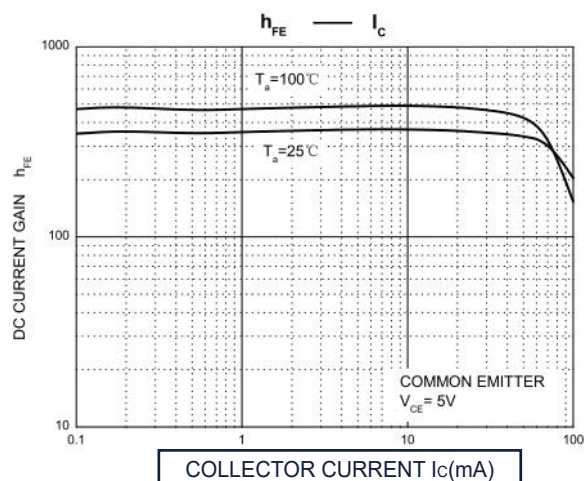
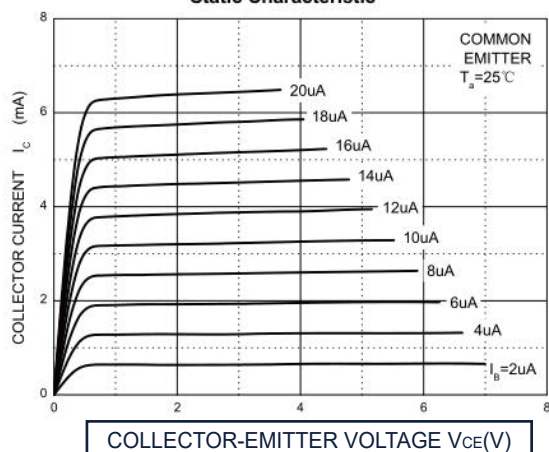
Ordering information

Product ID	Pack	Naming rule	Marking	hFE(1)	Qty(PCS)
BC847C	SOT23	BC847C ↓ 产品名称 product name	1G	200~450	3000



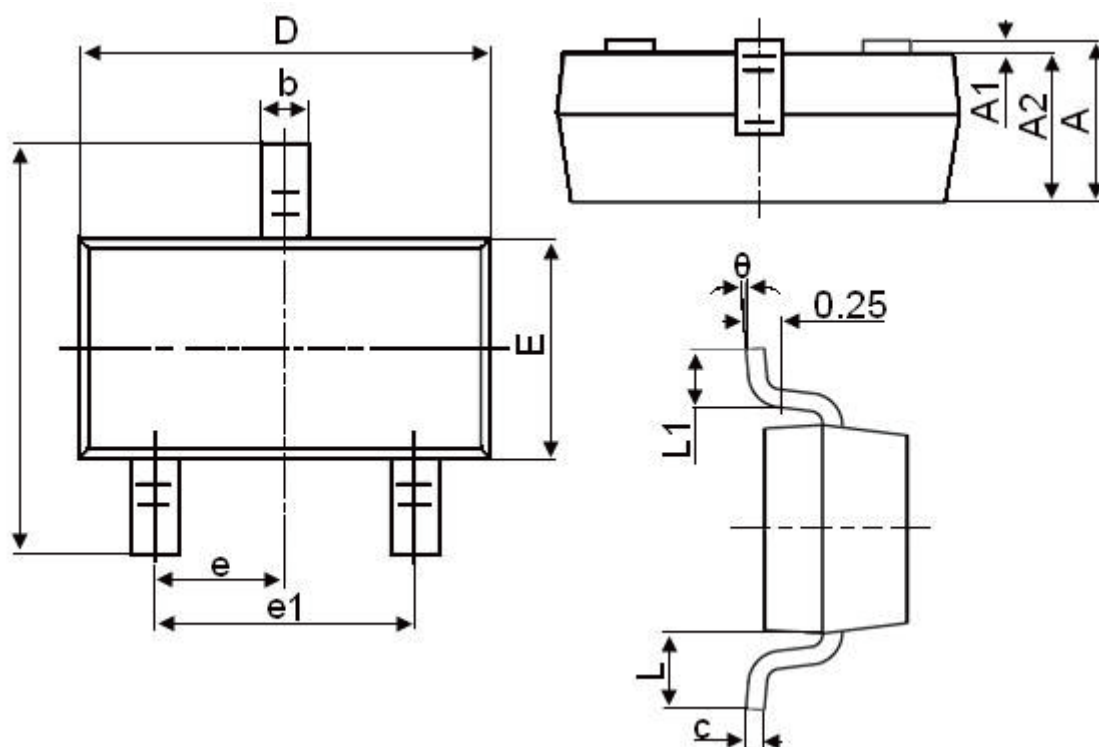
Typical Characteristics

Static Characteristic





SOT23 Package Outline Dimensions



Symbol	Dimensions in Millimeters	
	mm	
	Min	Max
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°